

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (canceled)
2. (currently amended) The package as set forth in claim [[1]] 5, wherein the cap structure has a cavity at a portion corresponding to the micro device.
3. (currently amended) The package as set forth in claim [[1]] 5, wherein the cap structure is a silicon wafer or glass wafer.
4. (canceled)
5. (currently amended) A wafer level package, comprising:
a device wafer having a micro device, and bonding pads connected to the micro device,
which are formed at one surface of the device wafer;
via connectors extending from the bonding pads to the other surface of the device wafer;
external bonding pads formed at the other surface of the device wafer and adapted to be
connected to the bonding pads through the via connectors, respectively;
a cap structure bonded to one surface of the device wafer so as to allow the micro device to
be insulated and hermetically sealed; and
a sealing member for bonding the cap structure to the device wafer;
The package as set forth in claim 4, wherein:

the device wafer further has a peripheral metal pad formed around a perimeter of one surface thereof to be bonded to the cap structure; and

the sealing member is a metal material formed on the peripheral metal pad.

6-7. (canceled)

8. **(currently amended)** The package as set forth in claim [[1]] 5, wherein the sealing is performed by an anodic bonding technique.

9. **(currently amended)** A wafer level package, comprising:
a device wafer having a micro device, and bonding pads connected to the micro device,
which are formed at one surface of the device wafer;
via connectors extending from the bonding pads to the other surface of the device wafer;
external bonding pads formed at the other surface of the device wafer and adapted to be
connected to the bonding pads through the via connectors, respectively; and
a cap structure bonded to one surface of the device wafer so as to allow the micro device to
be insulated and hermetically sealed;

~~The package as set forth in claim 1, wherein the cap structure has a dry film structure, the dry film structure having a well for receiving the micro device and bonding pads, and a passivation layer applied to an outer surface of the dry film structure.~~

10. (original) The package as set forth in claim 9, wherein the passivation layer is a material selected from among the group consisting of an epoxy resin, thermosetting resin, metal and photosensitive resin.

11-22. (canceled)

23. **(currently amended)** A wafer level package, comprising:
a device wafer having a micro device, and bonding pads connected to the micro device,
which are formed at one surface of the device wafer;

via connectors extending from the bonding pads to the other surface of the device wafer;
external bonding pads formed at the other surface of the device wafer and adapted to be
connected to the bonding pads through the via connectors, respectively;
a cap structure bonded to one surface of the device wafer so as to allow the micro device to
be insulated and hermetically sealed; and

~~The package as set forth in claim 1, further comprising~~ a first cavity defined between the
device wafer and the cap structure and a second cavity formed in the device wafer;
wherein said micro device is positioned between said first and second cavities.

24. **(currently amended)** The package as set forth in claim [[1]] 5, wherein said micro
device is a film bulk acoustic resonator (FBAR).

25. **(currently amended)** The package as set forth in claim [[1]] 5, further comprising
a cavity defined between the device wafer and the cap structure;
wherein said cavity is located corresponding to the micro device and the bonding pads; and
wherein said bonding pads are completely located in said cavity.

26. **(currently amended)** The package as set forth in claim [[1]] 5, wherein
said cap structure includes a depression having a bottom and side walls extending upwardly
from the bottom, said depression defining together with said device wafer a cavity accommodating
said micro device and bonding pads; and
an entirety of each of the bonding pads is inwardly spaced from a closest one of said side
walls.

27. (previously presented) The package as set forth in claim 9, wherein the dry film structure is photosensitive.

28. (previously presented) The package as set forth in claim 9, wherein the passivation layer is formed on and covers

a top surface of the cap structure,

side surfaces of the cap structure, said side surfaces extending downwardly from the top surface toward the device wafer, and

outer peripheral portions of the surface of the device wafer that is bonded to the cap structure.

29. (previously presented) A wafer level package, comprising:

a wafer having opposite upper and lower surfaces;

a micro device mounted on the upper surface of said wafer;

internal bonding pads positioned on the upper surface of said wafer and electrically connected to said micro device;

external bonding pads positioned on the lower surface of said wafer;

via connectors extending through said wafer from the upper surface to the lower surface and electrically connecting the internal bonding pads and the external bonding pads, respectively;

a cap structure bonded to the upper surface of said wafer and defining with said wafer a cavity in which said micro device is insulated and hermetically sealed;

wherein said internal bonding pads are completely located within said cavity.

30. (previously presented) The package as set forth in claim 29, further comprising another cavity formed in the upper surface of said wafer;

wherein said micro device is positioned between said cavities and spans over said another cavity.

31. (previously presented) The package as set forth in claim 30, wherein said micro device is a film bulk acoustic resonator (FBAR).

32. (previously presented) The package as set forth in claim 29, wherein said cap structure includes a depression having a top wall and side walls extending downwardly from the top wall, said depression defining together with said wafer said cavity; and an entirety of each of the internal bonding pads is inwardly spaced from a closest one of said side walls.

33. (previously presented) The package as set forth in claim 29, further comprising a passivation layer that is formed on and covers a top surface of said cap structure, side surfaces of said cap structure, said side surfaces extending downwardly from the top surface toward said wafer, and outer peripheral portions of the upper surface of said wafer, said outer peripheral portions surrounding a bonding region in which said cap structure and said wafer are sealingly bonded.

34. (new) The package as set forth in claim 29, further comprising: a sealing member for bonding the cap structure to the device wafer.

35. (new) The package as set forth in claim 34, wherein the sealing member is a glass frit.

36. (new) The package as set forth in claim 34, wherein the sealing member is a resin based adhesive.

37. (new) The package as set forth in claim 5, further comprising a first cavity defined

between the device wafer and the cap structure and a second cavity formed in the device wafer;
wherein said micro device is positioned between said first and second cavities.